



(19)

(11) Publication number:

05062911 A

Generated Document.

## PATENT ABSTRACTS OF JAPAN

(21) Application number: 03223234

(22) Application date: 04.09.91

(51) Int. Cl.: H01L 21/205 H01S 3/18

(30) Priority:

(43) Date of application  
publication: 12.03.93

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(84) Designated contracting  
states:

(74) Representative:

(54) MANUFACTURE OF  
SEMICONDUCTOR  
SUPERLATTICE

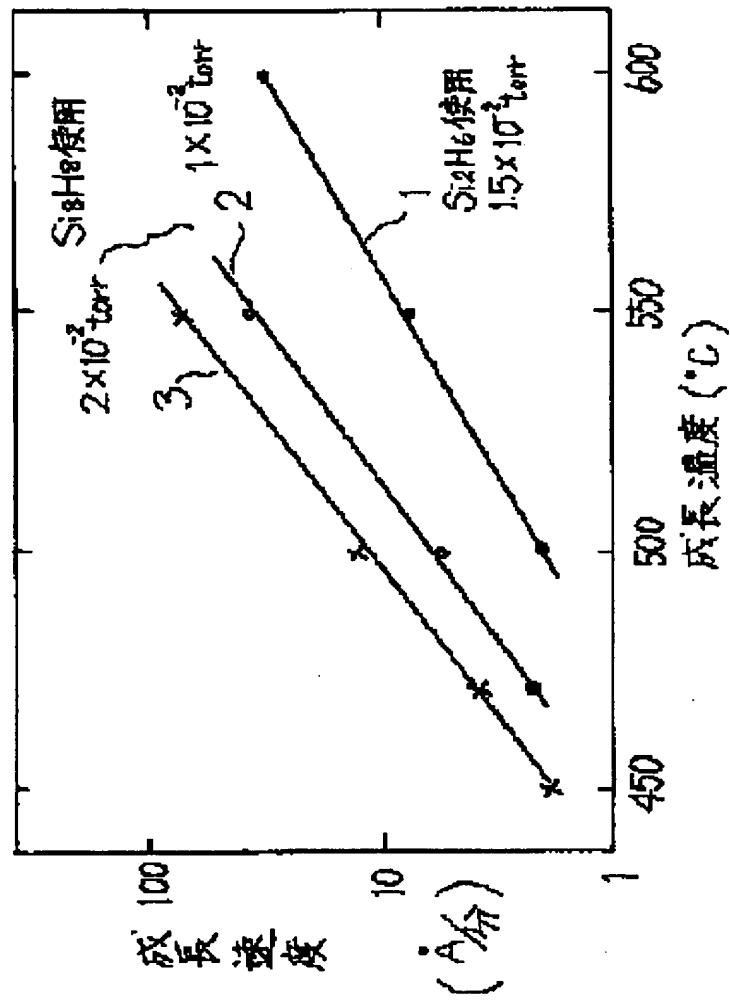
(57) Abstract:

PURPOSE: To form a Ge layer and an Si layer or a Ge-Si layer and an Si layer on an Si substrate, and also to put a hetero-epitaxial growth method, in which excellent crystal quality and high growth speed can be obtained, into practical use.

CONSTITUTION: The title  
semiconductor superlattice

manufacturing method is the method with which a Ge layer and an Si layer or Ge-Si layer and an Si layer are epitaxially grown on an Si substrate by conducting a depressed CVD method under the atmosphere containing oxidizing impurity gas of 1000ppb or lower using GeH<sub>4</sub> and trisilane (Si<sub>3</sub>H<sub>8</sub>) as raw gas and also using H<sub>2</sub> or inert gas as carrier gas.

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